

L Number	Hits	Search Text	DB	Time stamp
1	184	barrier same copper same anneal\$6 same (reducing or (forming adj gas) or ammonia or nitrogen or ("nh.sub.3") or ("n.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 08:16
2	94	(barrier same copper same anneal\$6 same (reducing or (forming adj gas) or ammonia or nitrogen or ("nh.sub.3") or ("n.sub.2")) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 08:16
-	833	438/618	USPAT; EPO; JPO; DERWENT	2003/03/10 10:42
-	672	438/633	USPAT; EPO; JPO; DERWENT	2001/12/17 14:40
-	45384	barrier adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:06
-	1055	(barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2004/03/02 08:58
-	237	((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:17
-	5	(barrier adj (layer or film)) and (first adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:56
-	0	((barrier adj (layer or film)) and (first adj reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:53
-	0	((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))) and (second adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:55
-	237	((barrier adj (layer or film)) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))) and (reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:55
-	163	(first adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 14:58
-	92	((first adj reduc\$4 adj (gas or agent or chemical))) and (second adj reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/17 15:01
-	6	((first adj reduc\$4 adj (gas or agent or chemical))) and (second adj reduc\$4 adj (gas or agent or chemical))) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/17 15:01
-	683	438/627	USPAT; EPO; JPO; DERWENT	2001/12/17 15:31
-	1178	438/643	USPAT; EPO; JPO; DERWENT	2002/01/02 14:19
-	20851	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:01
-	394	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (reduc\$4 adj (gas or agent or chemical))	USPAT; EPO; JPO; DERWENT	2001/12/18 08:17
-	96	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (reduc\$4 adj (gas or agent or chemical))) and (metal adj (film or layer))	USPAT; EPO; JPO; DERWENT	2001/12/18 12:54
-	20851	((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:02
-	3447	((diffus\$6 adj barrier) or (diffus\$6 adj prevent\$10)) adj (layer or film))	USPAT; EPO; JPO; DERWENT	2001/12/18 14:04

-	40	(((((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (first adj anneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:07
-	0	(((((diffus\$6 adj barrier) or prevent\$10) adj (layer or film))) and (first adj anneal\$5)) and (second adj aneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:08
-	45418	barrier adj (layer or film)	USPAT; EPO; JPO; DERWENT	2003/03/07 13:53
-	147	(barrier adj (layer or film)) and (first adj anneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:08
-	0	((barrier adj (layer or film)) and (first adj anneal\$5)) and (second adj aneal\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:21
-	483098	plug or interconnection	USPAT; EPO; JPO; DERWENT	2001/12/18 14:23
-	108014	metal adj (layer or film)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:24
-	18975	(metal adj (layer or film)) and (plug or interconnect\$5)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	3544	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5	USPAT; EPO; JPO; DERWENT	2001/12/18 14:25
-	56	((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5) and (reduc\$3 adj atmosphere)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:30
-	6	((barrier adj (layer or film)) and (first adj anneal\$5)) and (reduc\$3 adj atmosphere)	USPAT; EPO; JPO; DERWENT	2001/12/18 14:31
-	40	(((((metal adj (layer or film)) and (plug or interconnect\$5)) and anneal\$5) and (reduc\$3 adj atmosphere)) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/18 14:37
-	6	((barrier adj (layer or film)) and (first adj anneal\$5)) and (reduc\$3 adj atmosphere) and semiconductor	USPAT; EPO; JPO; DERWENT	2001/12/18 14:36
-	5	((("5116463") or ("6207222") or ("6197688") or ("6191031") or ("6143646")).PN.	USPAT	2004/07/22 09:35
-	562	438/687	USPAT; EPO; JPO; DERWENT	2004/02/20 13:52
-	55733	barrier adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 07:56
-	489	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:01
-	160	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:03
-	3	((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:08
-	222	(barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 14:05

-	3	(((((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 13:59
-	113	(((((barrier adj (layer or film)) and (reduc\$3 adj (gas or ambient))) and (metal adj (layer or film))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:06
-	28226	(barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:03
-	6490	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:05
-	222	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (reduc\$3 adj (gas or ambient)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:07
-	8105	((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:07
-	3403	(((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:07
-	99	(((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:07
-	99	(((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:10
-	92	(((((barrier adj (layer or film)) and (reduc\$3 or (hygrogen or ("H.sub.2"))) adj (gas or ambient))) and (metal adj (layer or film))) and (second adj (gas or ambient))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/07 14:10
-	25099	barrier adj (layer or film)	USPAT	2003/03/10 07:56
-	7320	(barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))))	USPAT	2003/03/10 08:01
-	3856	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor	USPAT	2003/03/10 08:02
-	1694	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))	USPAT	2003/03/10 08:03
-	303	((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))	USPAT	2003/03/10 08:04

-	60	(((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and (metal adj (layer or film))) and (second adj gas)	USPAT	2003/03/10 08:05
-	9	(((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas)	USPAT	2004/02/20 13:52
-	2	((("5665659") or ("5953634")).PN.	USPAT	2004/02/23 09:53
-	1	("6475902").PN.	USPAT	2003/11/17 07:10
-	1	("20020009872").PN.	US-PGPUB	2003/11/14 16:12
-	3	((("20020022354") or ("6248633") or ("6303959")).PN.	USPAT; US-PGPUB	2003/11/17 06:46
-	10	(((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas)	USPAT	2004/02/20 13:53
-	1661	438/687	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:52
-	1884	438/618	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:52
-	1281	438/633	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:52
-	1407	438/627	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:53
-	1772	438/643	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:53
-	1661	438/687	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:53
-	2	438/687,618,633,627,643,687.CCLS. and (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 13:03
-	8	438/\$.CCLS. and (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:58

-	8	257/\$.CCLS. and (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:59
-	11	(((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 13:59
-	5	("5139825" "5178911" "5856236" "5900498" "5908947").PN.	USPAT	2004/02/23 08:02
-	2508	(barrier adj (layer or film)) and (reduc\$4) and (metal adj (layer or film)) and (treat\$6 or ((post adj treat\$6) or (post-treat\$6) or (posttreat\$6)))	USPAT; EPO; JPO; DERWENT	2004/03/02 09:01
-	2198	(barrier adj (layer or film)) and (reduc\$4) and (metal adj (layer or film)) and (treat\$6 or ((post adj treat\$6) or (post-treat\$6) or (posttreat\$6))) and @ad<=20010417	USPAT; EPO; JPO; DERWENT	2004/03/02 09:02
-	1612	semiconductor and (barrier adj (layer or film)) and (reduc\$4) and (metal adj (layer or film)) and (treat\$6 or ((post adj treat\$6) or (post-treat\$6) or (posttreat\$6))) and @ad<=20010417	USPAT; EPO; JPO; DERWENT	2004/03/02 09:12
-	1416	(semiconductor and (barrier adj (layer or film)) and (reduc\$4) and (metal adj (layer or film)) and (treat\$6 or ((post adj treat\$6) or (post-treat\$6) or (posttreat\$6))) and @ad<=20010417) and expos\$6	USPAT; EPO; JPO; DERWENT	2004/03/02 09:13
-	1416	((semiconductor and (barrier adj (layer or film)) and (reduc\$4) and (metal adj (layer or film)) and (treat\$6 or ((post adj treat\$6) or (post-treat\$6) or (posttreat\$6))) and @ad<=20010417) and expos\$6) and reduc\$6	USPAT; EPO; JPO; DERWENT	2004/03/02 09:15
-	1	("5,953,634").PN.	USPAT	2004/03/02 12:53
-	1	("5,665,659").PN.	USPAT	2004/03/02 12:53
-	2	438/687,618,633,627,643,687.CCLS. and (((barrier adj (layer or film)) and ((expos\$3 or anneal\$5) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and semiconductor) and ((metal adj (layer or film)) same (chemical adj vapor adj deposition))) and (second adj gas) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:00
-	528	438/687,618,633,627,643,687.CCLS. and ((barrier or diffus\$5) adj (layer or film)) and (expos\$3 or treat\$6) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:03
-	3489	438/\$.CCLS. and ((barrier or diffus\$5) adj (layer or film)) and (expos\$3 or treat\$6) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:03
-	498	438/687,618,633,627,643,687.CCLS. and (barrier adj (layer or film)) and (expos\$3 or treat\$6) and ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 08:04
-	239	438/687,618,633,627,643,687.CCLS. and (barrier adj (layer or film)) and ((expos\$3 or treat\$6) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2"))))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 14:40
-	1	("6475902").PN.	USPAT	2004/03/08 11:14

-	2	((("6475902") or ("5665659")).PN.	USPAT	2004/07/16 12:19
-	885	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 07:04
-	260	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:07
-	7	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 08:27
-	13	438/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 09:07
-	15	257/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 09:07
-	18	semiconductor and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:25
-	35	438/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 09:08
-	42	257/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 09:08
-	51	semiconductor and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 09:08
-	543	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:09
-	275	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) and anneal\$5 and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:09
-	275	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) and anneal\$5 and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:10
-	190	438/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) with anneal\$5 and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:11
-	686	438/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) same anneal\$5 and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:12

-	938	257/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) same anneal\$5) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:12
-	256	257/\$.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) with anneal\$5) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:13
-	303	semiconductor and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) with anneal\$5) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:13
-	1034	semiconductor and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) same anneal\$5) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 11:13
-	144	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) same anneal\$5) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:19
-	0	20020009872.URPN.	USPAT	2004/07/16 13:48
-	12	semiconductor and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and anneal\$6 and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:26
-	32	semiconductor and ((barrier or (diffus\$6 adj prevent\$6)) same ((reduc\$3 adj gases) or (hydrogen or ("H.sub.2")))) and anneal\$6 and ((free or without or no) adj plasma) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:26
-	37	438/687,618,633,627,643,687.CCLS. and ((barrier or (diffus\$6 adj prevent\$6)) with ((reduc\$3 adj gases) or (nitrogen or ("n.sub.2")) or (hydrogen or ("H.sub.2")))) with anneal\$5) and @ad<=20010417	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/16 13:48
-	8	"6214730"	USPAT	2004/07/16 13:48
-	1	("6214730").PN.	USPAT	2004/07/21 14:33
-	1	("6310300").PN.	USPAT	2004/07/16 13:56
-	1	("6355558").PN.	USPAT	2004/07/16 13:56
-	6	((("6159857") or ("6350688") or ("20030015793") or ("20030034251") or ("6479340") or ("20020025694"))).PN.	USPAT; US-PGPUB	2004/07/22 08:13